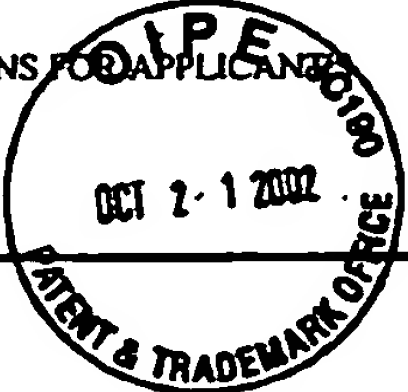






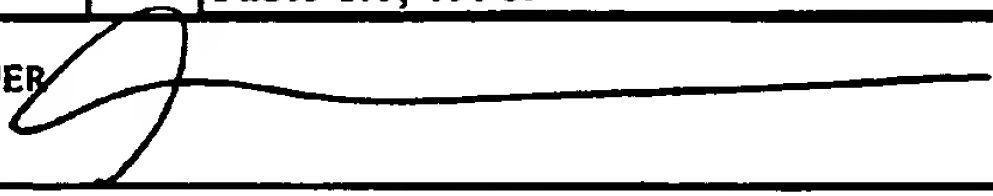
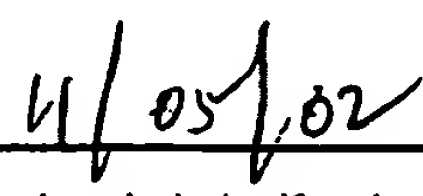
FORM PTO-1449 (Modified)		ATTY. DOCKET NO. YOR919990123US2		SERIAL NO.: 09/936,320	
LIST OF PATENTS AND PUBLICATIONS FOR APPLICANT'S INFORMATION DISCLOSURE STATEMENT		APPLICANT: Jack O. Chu			
(Use several sheets if necessary)		FILING DATE: September 12, 2001		GROUP: 2811	



REFERENCE DESIGNATION			U.S. PATENT DOCUMENTS				
EXAMINER INITIALS		DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE (IF APPRO.)
	BA						
	BB						
	BC						

FOREIGN PATENT DOCUMENTS							
		DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION
							YES NO
	BD						
	BE						
	BF						

OTHER ART (Including Author, Title, Date, Pertinent Pages, etc.)		
	BE	M. Arafa, "A 70-GHz f_T Low Operating Bias Self-Aligned p-Type SiGe MODFET"; IEEE Electron Device Letters; Vol. 17; No. 12; pp. 586-588; December 1996.
	BF	U. Kong et al., "SiGe HBTs And HFETs"; IEEE Solid State Electronics; Vol. 38; No. 9; pp. 1595-1602; Elsevier; 1995.
	BG	Milind Gokhale et al., "Enhanced Performance Of PMOS and CMOS Circuits Using Self-Aligned MOSFETs With Modulation Doped Si-Ge Channel"; Proceedings of the Tenth Biennial University/ Government/Industry Microelectronics Symposium; 1993 IEEE; US; New York; pp.219-222; May 18-19, 1993.
	BH	David W. Greve, "Field Effect Devices And Applications"; Prentice-Hall, Inc; Simon & Schuster/ A Viacom Company; Upper Saddle River, NJ, 07458; Chap. 8: Structure Of The GaAs MESFET; p.315; Table 8.1; 1998.

EXAMINER 	DATE CONSIDERED 
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EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.